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Amendments to the Claims

For convenience of the Examiner, the claims as amended in the Amendment filed December 1, 2003 are listed below:

1. (Previously Amended) A circuit arrangement (100) for protecting a chip arrangement (200), comprising:

at least one optosensitive detector unit (10), comprising at least one bipolar transistor, whose output voltage (V_{out}) is a measure of the incidence of light (L_i) on the detector unit (10), and

at least one comparator unit (20) preceded by the detector unit (10) provided for comparing the output voltage (V_{out}) of the detector unit (10) with a reference voltage (V_{ref}), wherein the data and/or functions of the chip arrangement (200) to be protected can be temporarily or permanently obstructed and/or erased (L) and/or blocked (S) and/or interrupted in the case of a failure message occurring during comparison of the output voltage (V_{out}) of the detector unit (10) with the reference voltage (V_{ref}).

2. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that the detector unit (10) is arranged

underneath at least an oxide layer of the chip arrangement (200), and/or substantially in the plane of the data and/or functions to be protected.

3. (Previously Cancelled).

4. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that the detector unit (10) is constituted by a plurality of spatially arranged bipolar transistors (12).

5. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that an emitter (124) of the bipolar transistor (12) is connected to the input (22), provided for the output voltage (V_{out}), of the comparator unit (20).

6. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that an emitter (124) of the bipolar transistor (12) is connected to at least a power supply voltage (V_{dd}) via at least a power supply resistor (14).

7. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that a collector (126) of the bipolar transistor (12) is connected to ground potential via at least a reference resistor (16).

8. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that a junction between a base (122) of the bipolar transistor (12) and a collector (126) of the bipolar transistor (12) is provided for absorbing the light incident on the detector unit (10).

9. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that the output voltage (V_{out}) of the detector unit (10) depends on a wavelength and/or an intensity of the incident light (L_i).

10. (Original) A circuit arrangement (100) as claimed in claim 1, characterized in that
at least an evaluation unit (30) is implemented and/or integrated in the comparator unit (20), or
the comparator unit (20) precedes at least an evaluation unit (30).

11. (Previously Amended) A circuit arrangement (100) as claimed in claim 10, characterized in that the evaluation unit (30) generates the failure message when the output voltage (V_{out}) of the detector unit (10) deviates from a nominal range.

12. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that

a working point of the detector unit (10) and/or
a threshold value of the reference voltage (V_{ref}) is adjustable.

13. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that at least a dielectric coating and/or a further protective coating which is provided for protecting the chip arrangement (200) from external influences is arranged within the chip arrangement (200) and/or laterally to the chip arrangement (200) and/or on the chip arrangement (200).

14. (Previously Amended) A circuit arrangement (100) as claimed in claim 13, characterized in that a material of the dielectric coating is epoxy resin or silicon nitride ($SiNO_2$) or silicon dioxide (SiO_2).

15. (Previously Amended) A circuit arrangement (100) as claimed in claim 13, characterized in that a material of the dielectric coating is substantially opaque.

16. (Previously Amended) A circuit arrangement (100) as claimed in claims 1, characterized in that the chip arrangement (200) is arranged on at least a layered carrier substrate of a semiconducting or insulating material.

17. (Previously Amended) A circuit arrangement (100) as claimed in claim 1, characterized in that the circuit arrangement (100) is implemented and/or integrated in a card.

18. (Previously Amended) A card, comprising the circuit arrangement (100) as claimed in claim 1.

19. (Previously Amended) A chip arrangement (200), comprising
at least one optosensitive detector units (10) as claimed in claim 1, and
at least a combination logic unit (40) for combining the detector units (10).
20. (Original) A chip arrangement (200) as claimed in claim 19, characterized in that the
combination logic unit (40) is connected to at least a control logic unit (50).
21. (Previously Amended) A chip arrangement (200) as claimed in claim 19, characterized in
that the combination logic unit (40) is connected to an electrically erasable storage unit (60).
22. (Previously Amended) A chip arrangement (200) as claimed in claim 21, characterized in
that the storage unit (60) is constituted by at least an EEPROM storage unit (60') (EEPROM =
Electrically Erasable Programmable Read-Only Memory), and the data and/or functions of the
chip arrangement (200) to be protected are erasable (L) when a failure message by means of the
EEPROM storage unit (60') occurs during comparison of the output voltage (V_{out}) of the detector
unit (10) with the reference voltage (V_{ref}).
23. (Previously Amended) A chip arrangement (200) as claimed in claim 20, characterized in
that
the storage unit (60) is arranged between the combination logic unit (40) and the
control logic unit (50), and
the access to the data and/or functions of the chip arrangement (200) to be
protected can be blocked by blocking (S) the storage unit (60) when a failure message occurs
during comparison of the output voltage (V_{out}) of the detector unit (10) with the reference voltage
(V_{ref}).

24. (Previously Amended) A chip arrangement (200) as claimed in claim 19, characterized in that the chip arrangement (200) can be permanently short-circuited via the power supply voltage (V_{dd}).

25. (Previously Amended) A method of protecting a chip arrangement (200), characterized in that

an output voltage (V_{out}) determined by light (L_i) incident on a detector unit (10) is generated in an optosensitive detector unit (10) comprising a bipolar transistor;

the output voltage (V_{out}) of the detector unit (10) is compared with a reference voltage (V_{ref}) in a comparator unit (20) preceded by the detector unit (10), and

the data and/or functions of the chip arrangement (200) to be protected are temporarily or permanently obstructed and/or erased (L) and/or blocked (S) and/or interrupted when a failure message is generated during comparison of the output voltage (V_{out}) of the detector unit (10) with the reference voltage (V_{ref}).

26. (Previously Amended) A method as claimed in claim 25, characterized in that the light incident on the detector unit (10) is substantially absorbed by means of a junction between a base (122) of the bipolar transistor (12) and a collector (126) of the bipolar transistor (12).

27. (Previously Amended) A method as claimed in claim 25, characterized in that the failure message is triggered in the comparator unit (20) when the output voltage (V_{out}) of the detector unit (10) deviates from a nominal range.

28. (Previously Amended) A method as claimed in claim 25, characterized in that the triggering of the failure message is adjusted by means of

a working point of the detector unit (10) and/or

a threshold value of the reference voltage (V_{ref}).

29. (Original) A method as claimed in claim 25, characterized in that the failure message is generated in at least

an evaluation unit (30) implemented and/or integrated in the comparator unit (20),

or

an evaluation unit (30) preceded by the comparator unit (20).

30. (Previously Amended) A method as claimed in claim 25, characterized in that a control logic unit (50) connected to a combination logic unit (40) provided for combining the detector units (10) is temporarily blocked (S) when the failure message is triggered.

31. (Previously Amended) A method as claimed in claim 25, characterized in that an electrically erasable storage unit (60) arranged between at least a combination logic unit (40) provided for combining the detector units (10) and a control logic unit (50) is permanently blocked (S) when the failure message is triggered.

32. (Original) A method as claimed in claim 31, characterized in that the control logic unit (50) is temporarily or permanently blocked (S) by means of at least a "reset" (RS).

33. (Previously Amended) A method as claimed in claim 25, characterized in that a once-electrically programmable storage unit (60) connected to a combination logic unit (40) provided for combining the detector units (10) is permanently blocked (S) when the failure message is triggered.

34. (Previously Amended) A method as claimed in claim 33, characterized in that the power supply voltage (V_{dd}) is short-circuited by means of the storage unit (60).

35. (Previously Amended) A method as claimed in claim 25, characterized in that the data and/or functions to be protected are erased (L) in an EEPROM storage unit (60') (EEPROM =

Electrically Erasable Programmable Read-Only Memory) connected to a combination logic unit (40) provided for combining the detector units (10) when the failure message is triggered.